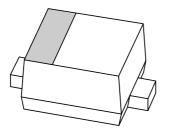
### **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# **PMEG2005EB**Low V<sub>F</sub> MEGA Schottky barrier diode

**Product specification** 

2003 Feb 20





## Low V<sub>F</sub> MEGA Schottky barrier diode

#### PMEG2005EB

#### **FEATURES**

• Forward current: 0.5 A • Reverse voltage: 20 V

- Very low forward voltage
- · Guard ring protected
- Ultra small SMD package.

#### **APPLICATIONS**

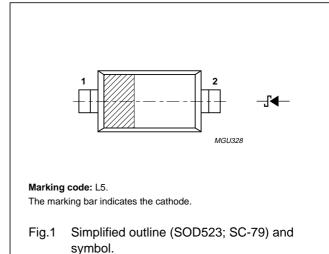
- Ultra high-speed switching
- Voltage clamping
- · Protection circuits
- · Low current rectification
- Low power consumption applications (e.g. handheld devices).

#### **DESCRIPTION**

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode, encapsulated in a SOD523 (SC-79) ultra small SMD plastic package.

#### **PINNING**

PIN	DESCRIPTION	
1	cathode	
2	anode	



symbol.

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>R</sub>	continuous reverse voltage		_	20	V
I <sub>F</sub>	continuous forward current		_	500	mA
I <sub>FRM</sub>	repetitive peak forward current	$t_p = 1 \text{ ms}; \delta \le 0.25$	_	3.5	Α
I <sub>FSM</sub>	non-repetitive peak forward current	t = 8 ms square wave	_	6	Α
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	125	°C
T <sub>amb</sub>	operating ambient temperature		-65	+125	°C

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# Low V<sub>F</sub> MEGA Schottky barrier diode

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#### **ELECTRICAL CHARACTERISTICS**

 $T_{amb}$  = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V <sub>F</sub>	continuous forward voltage	see Fig.2			
		I <sub>F</sub> = 0.1 mA	120	180	mV
		I <sub>F</sub> = 1 mA	180	240	mV
		I <sub>F</sub> = 10 mA	245	290	mV
		I <sub>F</sub> = 100 mA	320	380	mV
		I <sub>F</sub> = 500 mA	430	480	mV
I <sub>R</sub>	continuous reverse current	V <sub>R</sub> = 10 V; see Fig.3; note 1	7	30	μΑ
C <sub>d</sub>	diode capacitance	$V_R = 1 V$ ; $f = 1 MHz$ ; see Fig.4	24	30	pF

#### Note

1. Pulsed test:  $t_p = 300 \ \mu s$ ;  $\delta = 0.02$ .

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	400	K/W

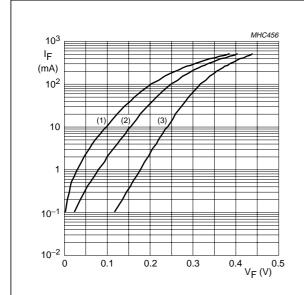
#### Note

1. Refer to SOD523 (SC-79) standard mounting conditions.

# Low V<sub>F</sub> MEGA Schottky barrier diode

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#### **GRAPHICAL DATA**



- (1)  $T_{amb} = 125 \,^{\circ}C$ .
- (2)  $T_{amb} = 85 \,^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .

Fig.2 Forward current as a function of forward voltage; typical values.

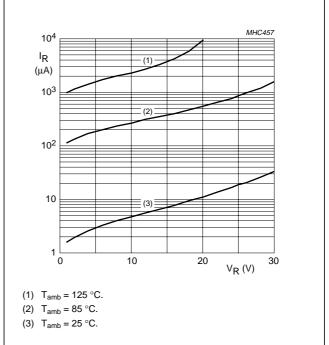
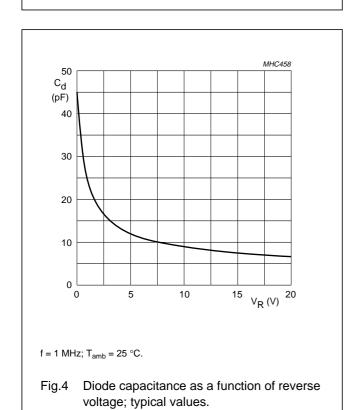


Fig.3 Reverse current as a function of reverse voltage; typical values.



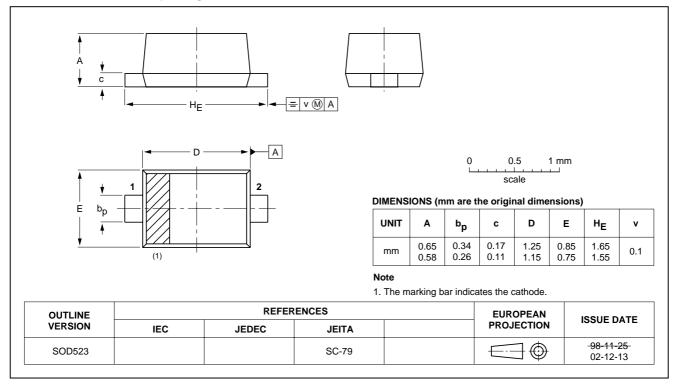
# Low V<sub>F</sub> MEGA Schottky barrier diode

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#### **PACKAGE OUTLINE**

#### Plastic surface mounted package; 2 leads

**SOD523** 



#### Low V<sub>F</sub> MEGA Schottky barrier diode

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#### **DATA SHEET STATUS**

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

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- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
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**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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# Low V<sub>F</sub> MEGA Schottky barrier diode

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**NOTES** 

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Printed in The Netherlands

613514/01/pp8

Date of release: 2003 Feb 20

Document order number: 9397 750 10776

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